

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China







IGBT

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Trench construction, and provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss.

Features

- Low Saturation Voltage using Trench with Field Stop Technology
- Low Switching Loss Reduces System Power Dissipation
- Optimized for High Speed Switching
- 5 µs Short-Circuit Capability
- These are Pb-Free Devices

Typical Applications

- Power Factor Correction
- Solar Inverters
- Uninterruptable Power Supply (UPS)

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-emitter voltage	V_{CES}	600	V
Collector current @ Tc = 25°C @ Tc = 100°C	I _C	100 50	Α
Pulsed collector current, T _{pulse} limited by T _{Jmax}	I _{CM}	200	Α
Short–circuit withstand time V_{GE} = 15 V, V_{CE} = 400 V, $T_{J} \le +150^{\circ}C$	t _{SC}	5	μS
Gate-emitter voltage	V_{GE}	±20	V
Power Dissipation @ Tc = 25°C @ Tc = 100°C	P_{D}	223 89	W
Operating junction temperature range	TJ	-55 to +150	°C
Storage temperature range	T _{stg}	-55 to +150	°C
Lead temperature for soldering, 1/8" from case for 5 seconds	T _{SLD}	260	°C

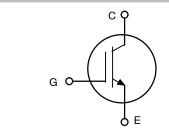
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

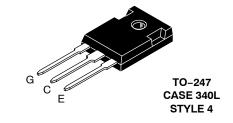


ON Semiconductor®

http://onsemi.com

50 A, 600 V V_{CEsat} = 1.65 V





MARKING DIAGRAM



A = Assembly Location

Y = Year WW = Work Week G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
NGTG50N60FLWG	TO-247 (Pb-Free)	30 Units / Rail

THERMAL CHARACTERISTICS

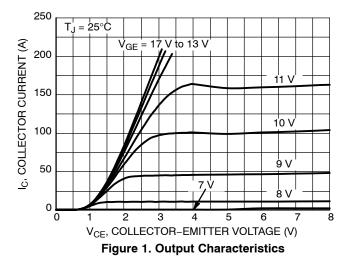
Rating	Symbol	Value	Unit
Thermal resistance junction-to-case, for IGBT	$R_{ heta JC}$	0.56	°C/W
Thermal resistance junction-to-ambient	$R_{ hetaJA}$	40	°C/W

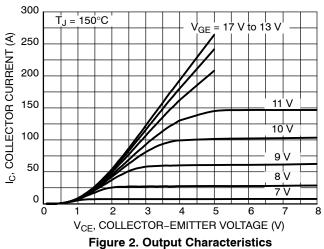
ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

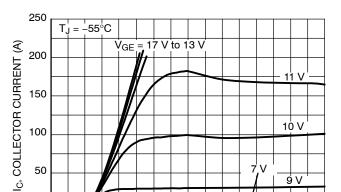
Parameter	Test Conditions	Symbol	Min	Тур	Max	Unit
STATIC CHARACTERISTIC	•	•		•		
Collector-emitter breakdown voltage, gate-emitter short-circuited	$V_{GE} = 0 \text{ V}, I_{C} = 500 \mu\text{A}$	V _{(BR)CES}	600	_	-	V
Collector-emitter saturation voltage	V _{GE} = 15 V, I _C = 50 A V _{GE} = 15 V, I _C = 25 A, T _J = 150°C	V _{CEsat}	1.40 –	1.65 1.85	1.90 –	V
Gate-emitter threshold voltage	$V_{GE} = V_{CE}, I_{C} = 350 \mu A$	V _{GE(th)}	4.5	5.5	6.5	V
Collector-emitter cut-off current, gate- emitter short-circuited	V _{GE} = 0 V, V _{CE} = 600 V V _{GE} = 0 V, V _{CE} = 600 V, T _J = 150°C	I _{CES}	- -	_ _	0.5 2	mA
Gate leakage current, collector–emitter short–circuited	V _{GE} = 20 V , V _{CE} = 0 V	I _{GES}	-	_	200	nA
DYNAMIC CHARACTERISTIC	•	•		•		
Input capacitance		C _{ies}	-	7302	_	pF
Output capacitance	V _{CE} = 20 V, V _{GE} = 0 V, f = 1 MHz	C _{oes}	-	220	_	
Reverse transfer capacitance	7	C _{res}	-	190	_	
Gate charge total		Q_g	-	310	_	nC
Gate to emitter charge	V _{CE} = 480 V, I _C = 50 A, V _{GE} = 15 V	Q _{ge}	-	60	_	
Gate to collector charge	7	Q _{gc}	-	150	_	
SWITCHING CHARACTERISTIC, INDUC	TIVE LOAD					
Turn-on delay time		t _{d(on)}	-	116	_	ns
Rise time	7	t _r	-	43	_	
Turn-off delay time	T _J = 25°C	t _{d(off)}	-	292	_	
Fall time	$V_{CC} = 400 \text{ V}, I_{C} = 50 \text{ A}$ $R_{c} = 10 \Omega$	t _f	-	78	_	
Turn-on switching loss	$R_g = 10 \Omega$ $V_{GE} = 0 \text{ V/ } 15 \text{ V*}$	E _{on}	-	1.1	_	mJ
Turn-off switching loss		E _{off}	-	0.6	_	
Total switching loss		E _{ts}	-	1.7	_	
Turn-on delay time		t _{d(on)}	-	110	_	ns
Rise time		t _r	_	45	_	
Turn-off delay time	T _J = 150°C	t _{d(off)}	-	300	_	
Fall time	$V_{CC} = 400 \text{ V}, I_{C} = 50 \text{ A}$ $R_{g} = 10 \Omega$	t _f	-	105	-	
Turn-on switching loss	$R_g = 10 \Omega$ $V_{GE} = 0 \text{ V/ } 15 \text{ V*}$	E _{on}	-	1.4	-	mJ
Turn-off switching loss		E _{off}	-	1.1	-	
Total switching loss		E _{ts}	-	2.5	_	

^{*}Includes diode reverse recovery loss using NGTB50N60FLWG.

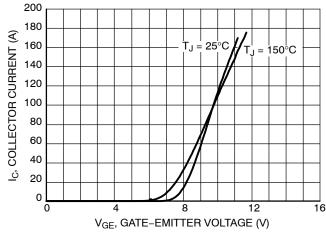
TYPICAL CHARACTERISTICS

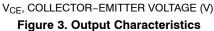




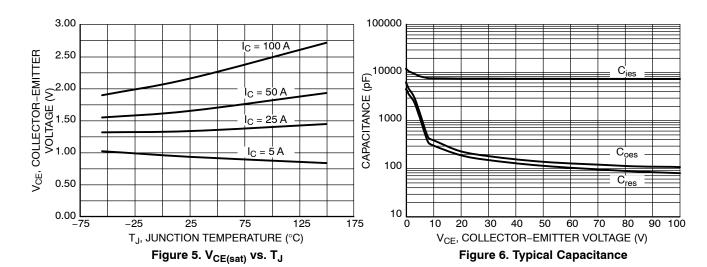


0









9 V

8 V

TYPICAL CHARACTERISTICS

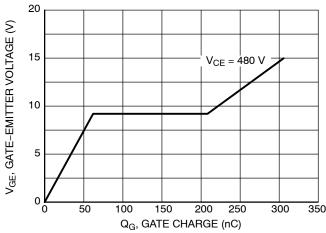


Figure 7. Typical Gate Charge

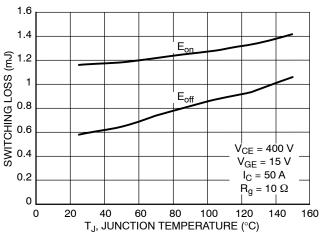


Figure 8. Switching Loss vs. Temperature

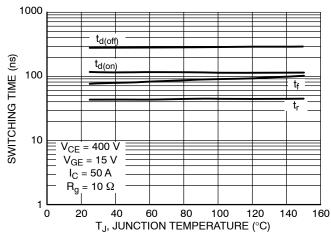


Figure 9. Switching Time vs. Temperature

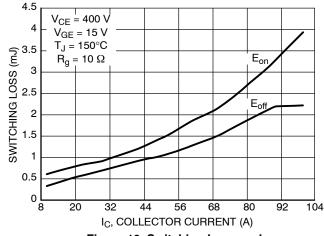


Figure 10. Switching Loss vs. I_C

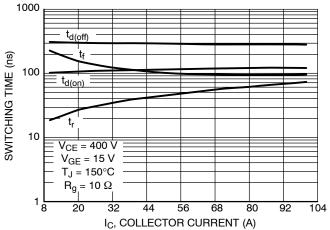


Figure 11. Switching Time vs. I_C

TYPICAL CHARACTERISTICS

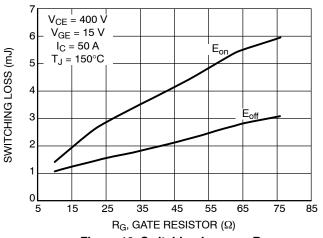


Figure 12. Switching Loss vs. $R_{\mbox{\scriptsize G}}$

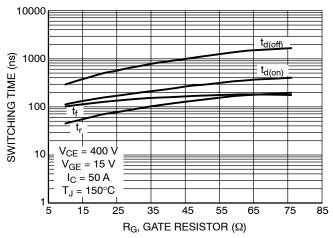


Figure 13. Switching Time vs. R_G

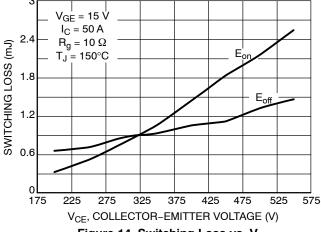


Figure 14. Switching Loss vs. V_{CE}

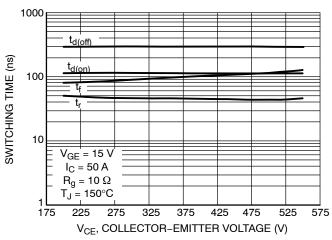
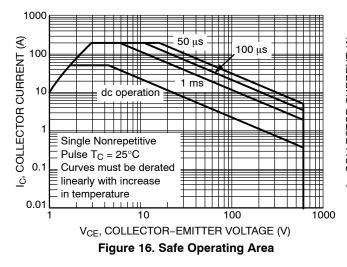


Figure 15. Switching Time vs. V_{CE}



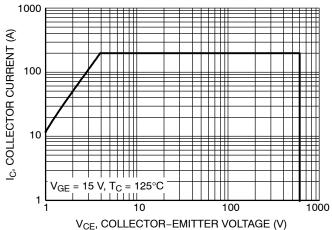


Figure 17. Reverse Bias Safe Operating Area

TYPICAL CHARACTERISTICS

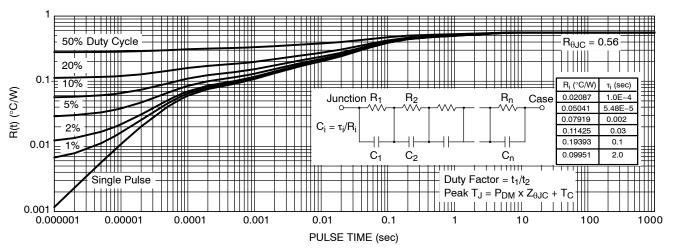


Figure 18. IGBT Transient Thermal Impedance

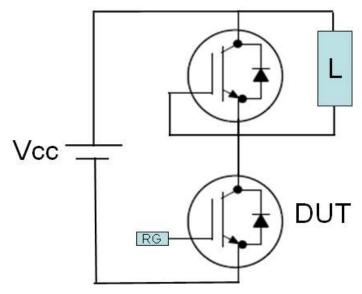


Figure 19. Test Circuit for Switching Characteristics

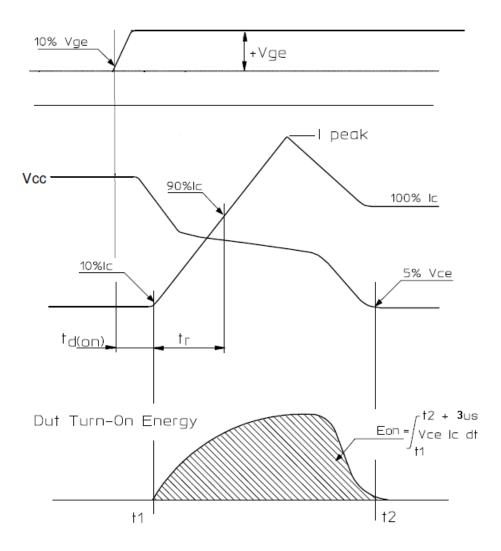


Figure 20. Definition of Turn On Waveform

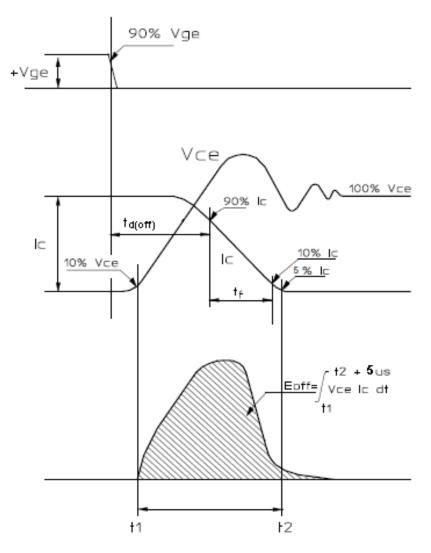
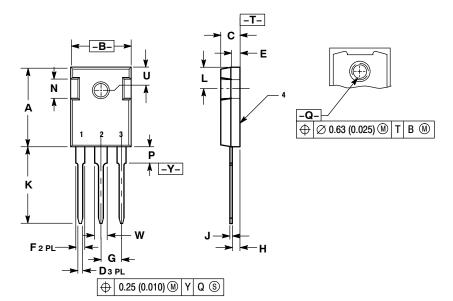


Figure 21. Definition of Turn Off Waveform

PACKAGE DIMENSIONS

TO-247 CASE 340L-02 ISSUE F



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	20.32	21.08	0.800	8.30	
В	15.75	16.26	0.620	0.640	
С	4.70	5.30	0.185	0.209	
D	1.00	1.40	0.040	0.055	
Е	1.90	2.60	0.075	0.102	
F	1.65	2.13	0.065	0.084	
G	5.45 BSC		0.215 BSC		
Н	1.50	2.49	0.059	0.098	
J	0.40	0.80	0.016	0.031	
K	19.81	20.83	0.780	0.820	
L	5.40	6.20	0.212	0.244	
N	4.32	5.49	0.170	0.216	
P		4.50		0.177	
Q	3.55	3.65	0.140	0.144	
U	6.15	BSC	0.242 BSC		
W	2.87	3.12	0.113	0.123	

STYLE 4:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
COLLECTOR

ON Semiconductor and un are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, one semiconductor and are registered traderinats of semiconductor Components mustures. Let (ScillLC) scill science of the copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent—Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surviced implant into the policy or other applications intended for surviced implant into the policy or other applications intended for surviced implant into the policy or other applications. surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and resanchable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada

Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center

Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative